

Alexey Chernykh

List of Publications by Citations

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30
papers

353
citations

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h-index

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33
ext. papers

442
ext. citations

2.7
avg, IF

3.44
L-index

#	Paper	IF	Citations
30	Electrical properties of bulk semi-insulating FeGa_2O_3 (Fe). <i>Applied Physics Letters</i> , 2018 , 113, 142102	3.4	59
29	Hole traps and persistent photocapacitance in proton irradiated FeGa_2O_3 films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
28	Hydrogen plasma treatment of FeGa_2O_3 : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , 2019 , 115, 032101	3.4	29
27	Electrical properties, structural properties, and deep trap spectra of thin FeGa_2O_3 films grown by halide vapor phase epitaxy on basal plane sapphire substrates. <i>APL Materials</i> , 2018 , 6, 121110	5.7	26
26	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski FeGa_2O_3 (Mg). <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3019-Q3023	2	25
25	Defects at the surface of FeGa_2O_3 produced by Ar plasma exposure. <i>APL Materials</i> , 2019 , 7, 061102	5.7	25
24	Deep trap spectra of Sn-doped FeGa_2O_3 grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , 2019 , 7, 051103	5.7	22
23	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating FeGa_2O_3 Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3091-Q3096	2	19
22	Anisotropy of hydrogen plasma effects in bulk n-type FeGa_2O_3 . <i>Journal of Applied Physics</i> , 2020 , 127, 175702	2.5	14
21	Photosensitivity of Ga_2O_3 Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
20	Pulsed fast reactor neutron irradiation effects in Si doped n-type FeGa_2O_3 . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
19	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in FeGa_2O_3 vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
18	Electric field dependence of major electron trap emission in bulk FeGa_2O_3 : Poole-Frenkel effect versus phonon-assisted tunneling. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 304001	3	9
17	Experimental estimation of electron-hole pair creation energy in FeGa_2O_3 . <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8
16	Schottky contacts to high-resistivity epitaxial GaAs layers for detectors of particles and X- or γ -ray photons. <i>Semiconductors</i> , 2012 , 46, 1066-1071	0.7	6
15	Investigation of the thermal annealing effect on electrical properties of Ni/Au, Ni/Mo/Au and Mo/Au Schottky barriers on AlGaN/GaN heterostructures. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012039	0.3	4
14	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of FeGa_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P661-P666	2	4

13	Crystal orientation dependence of deep level spectra in proton irradiated bulk $\text{E}\text{Ga}_2\text{O}_3$. <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
12	Halide Vapor Phase Epitaxy of In_2O_3 and $(\text{In}_{1-x}\text{Ga}_x)_2\text{O}_3$ on Sapphire Substrates and $\text{GaN}/\text{Al}_2\text{O}_3$ Templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000442	1.6	2
11	Fast-Neutron Detectors Based on Surface-Barrier GaAs Sensors with an Ultrahigh-Molecular-Weight Polyethylene Converter. <i>Instruments and Experimental Techniques</i> , 2019 , 62, 312-316	0.5	1
10	Deep traps and persistent photocapacitance in $\text{E}(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterojunctions. <i>Journal of Applied Physics</i> , 2019 , 125, 095702	2.5	1
9	1 GeV proton damage in $\text{E}\text{Ga}_2\text{O}_3$. <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
8	Parasitic $p\bar{n}$ junctions formed at V-pit defects in p-GaN. <i>Journal of Applied Physics</i> , 2021 , 129, 155702	2.5	1
7	Mo/Al/Mo/Au-based ohmic contacts to AlGaIn/GaN heterostructures. <i>Russian Microelectronics</i> , 2016 , 45, 402-409	0.5	1
6	Electrical properties of $\text{E}\text{Ga}_2\text{O}_3$ films grown by halide vapor phase epitaxy on sapphire with $\text{E}\text{Cr}_2\text{O}_3$ buffers. <i>Journal of Applied Physics</i> , 2022 , 131, 215701	2.5	1
5	Structural and electrical properties of thick $\text{E}\text{Ga}_2\text{O}_3$ grown on GaN/sapphire templates. <i>APL Materials</i> , 2022 , 10, 061102	5.7	1
4	Testing of a Prototype Detector of Heavy Charged Particles Based on Diamond Epitaxial Films Obtained by Gas-Phase Deposition. <i>Instruments and Experimental Techniques</i> , 2019 , 62, 473-479	0.5	0
3	Comparative Characteristics of GaAs Detectors and Silicon Pixel Detectors with Internal Amplification. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1108, 1		
2	Detectors on the Basis of High-Purity Epitaxial GaAs Layers for Spectrometry of X and Gamma Rays. <i>Instruments and Experimental Techniques</i> , 2018 , 61, 665-672	0.5	
1	GaAs Schottky Barrier Detectors for Alpha-Particle Spectrometry at Temperatures up to 120°C. <i>Technical Physics Letters</i> , 2018 , 44, 942-945	0.7	